## NSN 5961-01-184-5458

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-184-5458 **Inclosure Material:** Ceramic **Overall Length:** 0.125 inches **Overall Diameter:** 0.093 inches **Internal Configuration:** Junction contact **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Gallium arsenide Voltage Rating In Volts Per Characteristic: 3.0 reverse voltage, dc **Current Rating Per Characteristic:** 150.00 milliamperes source cutoff current preset **Power Rating Per Characteristic:** 350.0 milliwatts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius ambient air **Special Features:** Junction pattern arrangement: pn **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli Fiig:

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